

substitute form PTO-1449

INFORMATION DISCLOSURE
STATEMENT BY APPLICANT



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Filing Date	October 31, 2003
First Named Inventor	Zechner
Group Art Unit	
Examiner Name	
Attorney Docket Number	5358

U.S. PATENT DOCUMENTS					
Init.		Number	Patentee	Publ'n Date	Relevant Portion
	A				
	B				
	C				
	D				

FOREIGN PATENT DOCUMENTS						
	E	EP	0862126	Asada et al.	26 Feb 1998	
	F	EP	0864991	Sakamoto	10 Mar 1998	
	G					

OTHER DOCUMENTS		
	H	G.L. Olson et al.: Kinetics of solid phase crystallization in amorphous silicon; Material Science Reports; Vol. 3, No. 1, June 1988
	I	P.M. Fahey et al.: Point defects and dopant diffusion in silicon; Reviews of Modern Physics; Vol. 61, No. 2, April 1989
	J	A.A. Wheeler et al.: Phase-field model for isothermal phase transitions in binary alloys; Physical Review A; Vol. 45, No. 10, May 15, 1992
	K	H.-D. Geiler, FSU Jena, GDR: Theoretical description of explosive crystallization phenomena induced by high temperature pulses in thin layers of amorphous semiconductors
	L	Hideki Takeuchi, Pushkar Ranade, and Tsu-Jae King: Suppression of Boron TED by Low Temperature SPC Anneal Prior to Dopant Activation; IEEE Transactions On Electron Devices, Vol. 29, No. 12, December 2002

Examiner Signature		Date Considered
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